

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d



#### Features

- Fully Integrated, High-Efficiency Charger for Single-Cell Li-Ion and Li-Polymer Battery Packs
- Faster Charging than Linear
- Charge Voltage Accuracy: ±0.5% at 25°C ±1% from 0 to 125°C
- ±5% Charge Current Regulation Accuracy
- 20 V Absolute Maximum Input Voltage
- 6.8 V Maximum Input Operating Voltage
- 1.5 A Maximum Charge Rate
- Charge and Mode Programmable through High-Speed I<sup>2</sup>C Interface (3.4 Mb/s) with Fast Mode Plus Compatibility
  - Fast Charge / Termination Current
  - Charger Voltage
  - Safety Timer
  - Termination Enable
- 3 MHz Synchronous Buck PWM Controller with Wide Duty Cycle Range
- Small-Footprint, 1µH External Inductor
- Safety Timer with Reset Control
- Low Reverse Leakage to Prevent Battery Drain to VIN

### **Applications**

- Cell Phones, Smart Phones, PDAs
- Digital Cameras
- Portable Media Players

## Description

The FAN5421 is a highly integrated switched-mode charger that minimizes single-cell Li-lon charging time.

The charging parameters and operating modes are programmable through an  $I^2C$  interface that operates up to 3.4 Mbps. The charger circuit switches at 3 MHz to minimize the size of external passive components.

The FAN5421 provides battery charging in three phases: conditioning, constant current, and constant voltage.

Charge termination is determined by a programmable minimum current level. A safety timer with reset control provides a safety backup for the  $I^2C$  host.

The IC automatically adapts to current-limited power sources by reducing the charge current to keep the input supply above a programmed voltage (default 4.52 V).

The IC automatically restarts the charge cycle when the battery falls below an internal threshold. If the input source is removed, the IC enters a high-impedance mode with leakage from the battery to the input prevented. Charge status is reported back to the host through the  $I^2C$  port. Charge current is reduced when the die temperature reaches 120°C.

The FAN5421 is available in a 1.96 x 1.87 mm, 20-bump, 0.4 mm pitch, Wafer-Level Chip-Scale Package (WLCSP).



#### Figure 1. Typical Application

Table 1. Ordering Information									
Part Number	Temperature Range	Package	PN Bits: IC_INFO[4:3]	Packing					
FAN5421BUCX <sup>(1)</sup>	-40 to 85°C	WLCSP-20, 0.4 mm Pitch	00	Tape and Reel					

Note:

1. Includes backside laminate



Component	Description	Vendor	Parameter	Тур.	Units
L1	1 μH ±20%, 1.6 A DCR = 55 mΩ, 2520	Murata: LQM2HPN1R0	1	1.0	
	1 μH ±30%, 1.4 A DCR = 85 mΩ, 2016	Murata: LQM2MPN1R0	L	1.0	μH
C <sub>IN1</sub>	1.0 μF, 10%, 25 V, X5R, 0603	Murata GRM188R61E105K TDK:C1608X5R1E105M	С	1.0	μF
C <sub>IN2</sub>	4.7 μF, 10%, 25 V, X5R, 0805	Murata: GRM21BR61E475K TDK: C2012X5R1E475K	С	4.7	μF
C <sub>BAT</sub>	10 μF, 20%, 6.3 V, X5R, 0603	Murata: GRM188R60J106M TDK: C1608X5R0J106M	С	10.0	μF
C <sub>OUT</sub>	0.1 μF, 10%, 6.3 V, X5R, 0402	Any	С	0.1	μF
CBOOT	10 nF, 10%, 6.3 V, X5R, 0402	Any	С	1.0	nF
C <sub>REF</sub>	1 μF, 10%, 6.3 V, X5R, 0402	Any	С	1.0	μF

# **Pin Configuration**

VI	N	BQQT	SCL
(A1)	(A2)	(A3)	(A4)
	<u></u>	$\sim$	~
	PMID		SDA
(B1)	(B2)	(B3)	(B4)
U.			S.
	SW		STAT
(C1)	(C2)	(C3)	(C4)
U	(02)	(0)	U.
	PGND		SRST
60			
(D1)	(D2)	(D3)	
CSIN	DIS	VREF	VBAT
(E1)	(E2)	(E3)	(E4)
·	·	·	·

Figure 4. Top View



Figure 5. Bottom View

# **Pin Definitions**

Pin #	Name	Description
A1, A2	VIN	<b>Charger Input Voltage</b> . Bypass with a 1 μF capacitor to PGND.
A3	BOOT	BOOT. High-side NMOS driver supply. Connect a 10nF capacitor from SW to this pin.
A4	SCL	SCL. I <sup>2</sup> C interface serial clock. This pin should not be left floating.
B1-B3	PMID	<b>Power Input Voltage</b> . Power input to the charger regulator, bypass point for the high-voltage input switch. Bypass with a minimum of 4.7 $\mu$ F capacitor to PGND.
B4	SDA	<b>SDA</b> . I <sup>2</sup> C interface serial data. This pin should not be left floating.
C1-C3	SW	Switching Node. Connect to output inductor.
C4	STAT	Status. Open-drain output indicating charge status. The IC pulls this pin LOW when charge is in process.
D1-D3	PGND	<b>Power GND</b> . Power return for gate drive and power transistors. The connection from this pin to the bottom of $C_{IN2}$ should be as short as possible.
D4	SRST	<b>Safety Reset</b> . When LOW, this pin resets the safety register to its default values. When HIGH, the safety register is reset when $V_{BAT}$ drops below $V_{SHORT}$ .
E1	CSIN	<b>Current Sense Input</b> . Connect to the sense resistor in series with the battery. The IC uses this node to sense current into the battery. Bypass this pin with a 0.1 $\mu$ F capacitor to PGND.
E2	DIS	<b>Charge Disable</b> . If this pin is HIGH, charging is disabled. When LOW, charging is controlled by the I <sup>2</sup> C registers. When this pin is HIGH, the 15-minute timer is reset; it does not affect the 32-second timer.
E3	VREF	<b>Bias Regulator Output</b> . Connect to a 1 $\mu$ F capacitor to PGND. This pin supplies the internal gate drive and power supply to the IC while charging. Up to 1 mA of current can be provided from this pin to drive the external circuits.
E4	VBAT	<b>Battery Voltage</b> . Connect to the positive (+) terminal of the battery pack. Bypass with a minimum of 10 $\mu$ F to PGND.

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter	Min.	Max.	Unit	
V		Continuous	-1.4	20.0	V	
V <sub>IN</sub>	VIN Voltage	Pulsed, 100 ms Maximum, Non-Repetitive	-2.0	20.0	V	
V <sub>STAT</sub>	STAT Voltage		-0.3	20.0	V	
V	PMID		-0.3	20.0	v	
VI	CSIN, VBAT, DISABLE		-0.3	7.0	v	
Vo	Other Pins		-0.3	6.5 <sup>(2)</sup>	V	
$\frac{dV_{IN}}{dt}$	Maximum Rate of $V_{IN}$ Increase Above 10 V When IC Enabled			4	V/µs	
	Electrostatic Discharge Human Body Model per JESD22-A114		2.5		1.3.7	
ESD	Protection Level	Charged Device Model per JESD22-C101	1.0		kV	
TJ	Junction Temperature		-40	+150	°C	
T <sub>STG</sub>	Storage Temperature		-65	+150	°C	
TL	Lead Soldering Temperature	e, 10 Seconds		+260	°C	

Note:

2. Lesser of 6.5 V or  $V_{\text{IN}}$  + 0.3 V.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	4.0	6.8	V
T <sub>A</sub>	Ambient Temperature	-30	+85	°C
TJ	Junction Temperature	-30	+120	°C

# **Thermal Properties**

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature  $T_{J(max)}$  at a given ambient temperature,  $T_A$ .

Symbol	Parameter	Typical	Unit
θја	Junction-to-Ambient Thermal Resistance	60	°C/W
$\theta_{JB}$	Junction-to-PCB Thermal Resistance	20	°C/W

# **Electrical Specifications**

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for  $T_J$  and  $T_A$ ,  $V_{IN}$  = 5.0 V, CE# = HZ\_MODE = 0, (Charger Mode operation). SCL, SDA, and SRST = 0 or 1.8 V; typical values are for  $T_J$  = 25°C.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Power Su	oplies		•	•		
		V <sub>IN</sub> > V <sub>IN(min)</sub> , PWM Switching		40		mA
	VIN Current	V <sub>IN</sub> > V <sub>IN(min)</sub> , PWM Not Switching		300		μA
IVIN	Villent	$0^{\circ}C < T_{J} < 85^{\circ}C, HZ_MODE = 1,$ V <sub>BAT</sub> > V <sub>LOWV</sub>		300		μA
I <sub>LKG</sub>	VBAT to VIN Leakage Current	0°C < T <sub>J</sub> < 85°C, HZ_MODE = 1, V <sub>BAT</sub> = 4.2 V			5	μA
	Battery Discharge Current in	$0^{\circ}C < T_J < 85^{\circ}C, HZ_MODE = 1, V_{BAT} = 4.2 V$			20	μA
I <sub>BAT</sub>	High-Z Mode	$\label{eq:basic} \begin{split} DISABLE &= 1, 0^\circ C < T_J < 85^\circ C, \\ V_{BAT} &= 4.2 \; V \end{split}$			10	μA
Charger V	oltage Regulation				-	
	Charge Voltage Range		3.5		4.4	V
$V_{\text{OREG}}$	Charge Voltage Accuracy	$T_A = 25^{\circ}C$ , <95% Duty Cycle	-0.5		+0.5	%
	Charge Vollage Accuracy	$T_J$ = 0 to 125°C, <95% Duty Cycle	-1		+1	/0
Charging	Current Regulation					
	Output Charge Current Range	$\label{eq:VLOWV} \begin{split} V_{\text{LOWV}} &< V_{\text{BAT}} < V_{\text{OREG}}, \ V_{\text{IN}} > V_{\text{SLP}}, \\ R_{\text{SENSE}} &= 68 \ m\Omega, \ <95\% \ \text{Duty Cycle} \end{split}$	550		1550	mA
I <sub>OCHRG</sub>	Charge Current Accuracy Across R <sub>SENSE</sub>	20 mV <u>&lt;</u> V <sub>RSENSE</sub> <u>&lt;</u> 40 mV	92	97	102	% of
		V <sub>RSENSE</sub> > 40 mV	94	97	100	Setting
Weak Batt	ery Detection			•		
	Weak Battery Threshold Range		3.4		3.7	V
$V_{\text{LOWV}}$	Weak Battery Threshold Accuracy	V <sub>BAT</sub> Falling	-5		+5	%
	Weak Battery Deglitch Time	Rising Voltage, 2mV Overdrive		30		ms
Logic Lev	els: DISABLE, SDA, SCL, SRST					
V <sub>IH</sub>	HIGH-Level Input Voltage		1.05			V
VIL	LOW-Level Input Voltage				0.4	V
I <sub>IN</sub>	Input Bias Current	Input Tied to GND or VIN		0.01	1.00	μA
Charge Te	ermination Detection					
	Termination Current Range	$V_{BAT} > V_{OREG} - V_{RCH},$ $V_{IN} > V_{SLP}, R_{SENSE} = 68 \text{ m}\Omega$	50		400	mA
	Termination Current Accuracy	$[V_{CSIN} - V_{BAT}]$ from 3 mV to 20 mV	-25		+25	0/
I <sub>(TERM)</sub>	Across R <sub>SENSE</sub>	$[V_{CSIN} - V_{BAT}]$ from 20 mV to 40 mV	-5		+5	%
	Termination Current Deglitch Time	2mV Overdrive		30		ms
VREF Pin						
		$I_{REF}$ from 0 to 1 mA, PMID $\geq$ 5.6 V			5.4	V
$V_{REF}$	VREF Pin Output Voltage	I <sub>REF</sub> from 0 to 1 mA, PMID < 5.6 V		PMID – 350		mV
	Short-Circuit Current Limit			15	1	mA

www.fairchildsemi.com

# **Electrical Specifications**

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for  $T_J$  and  $T_A$ ,  $V_{IN}$  = 5.0 V, CE# = HZ\_MODE = 0, (Charger Mode operation). SCL, SDA, and SRST = 0 or 1.8 V; typical values are for  $T_J$  = 25°C.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Uni
Input Pow	er Source Detection					1
VIN(MIN)1	V <sub>IN</sub> Input Voltage Rising	To Start VIN Validation	4.21	4.29	4.37	V
V <sub>IN(MIN)2</sub>	Minimum V <sub>IN</sub> to Pass Validation	During VIN Validation Period	4.00	4.08	4.15	V
V <sub>IN(MIN)3</sub>	Minimum V <sub>IN</sub> During Charge	During Charging	3.63	3.71	3.78	V
t <sub>VIN_VALID</sub>	V <sub>IN</sub> Validation Time			30		ms
Special Ch	harger		1		1	
$V_{\text{SP}}$	Special Charger Setpoint Accuracy		-3		+3	%
Battery Re	echarge Threshold					•
V <sub>RCH</sub>	Recharge Threshold	Below V <sub>(OREG)</sub>	100	120	150	mV
t <sub>G</sub>	Deglitch Time	V <sub>BAT</sub> Falling Below V <sub>RCH</sub> Threshold		130		ms
STAT Out	put		1		1	
V <sub>STAT(OL)</sub>	STAT Output Low	I <sub>STAT</sub> = 10 mA			0.4	V
I <sub>STAT(OH)</sub>	STAT High Leakage Current	V <sub>STAT</sub> = 5 V			1	μA
Battery De	etection					
IDETECT	Battery Detection Current Before Charge Done (Sink Current) <sup>(3)</sup>	Begins After Termination Detected and		-0.80		mA
t <sub>DETECT</sub>	Battery Detection Time	Vbat ≤ Voreg − Vrch		262		ms
Sleep Com	nparator		1		1	1
V <sub>SLP</sub>	Sleep-Mode Entry Threshold, $V_{IN} - V_{BAT}$	2.3 V $\leq$ V <sub>BAT</sub> $\leq$ V <sub>OREG</sub> , V <sub>IN</sub> Falling	0	0.04	0.10	V
	Sleep-Mode Exit Hysteresis	2.3 V ≤ V <sub>BAT</sub> ≤ V <sub>OREG</sub>	40	100	160	m۷
$V_{\text{SLP}\_\text{EXIT}}$	Deglitch Time for $V_{IN}$ Rising Above $V_{SLP} + V_{SLP\_EXIT}$	Rising Voltage		30		ms
Power Swi	itches (see Figure 3)		1		1	
	Q3 On Resistance (VIN to PMID)			180	250	mΩ
R <sub>DS(ON)</sub>	Q1 On Resistance (PMID to SW)			130	225	mΩ
	Q2 On Resistance (SW to GND)			175	225	mΩ
Charger P	WM Modulator					•
f <sub>SW</sub>	Oscillator Frequency		2.7	3.0	3.3	MH
$D_{MAX}$	Maximum Duty Cycle				99.6	%
D <sub>MIN</sub>	Minimum Duty Cycle		0			%
I <sub>SYNC</sub>	Synchronous to Non- Synchronous Current Cut-Off Threshold <sup>(4)</sup>	Low-Side MOSFET Cycle-by-Cycle Current Limit		170		mA
V <sub>IN</sub> Load R	lesistance					
D.		Normal Operation	650	1300	1950	KΩ
R <sub>VIN</sub>	VIN to PGND Resistance	Charger Validation	50	110	175	Ω

# **Electrical Specifications**

Unless otherwise specified: circuit of Figure 1, recommended operating temperature range for  $T_J$  and  $T_A$ ,  $V_{IN}$  = 5.0 V, CE# = HZ\_MODE = 0, (Charger Mode operation). SCL, SDA, and SRST = 0 or 1.8 V; typical values are for  $T_J$  = 25°C.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Protection	and Timers		•		•	
V	VIN Over-Voltage Shutdown	V <sub>IN</sub> Rising	6.83	7.03	7.23	V
VINOVP	Hysteresis	V <sub>IN</sub> Falling		130		mV
I <sub>LIMPK(CHG)</sub>	Q1 Cycle-by-Cycle Peak Current Limit	Charge Mode		2.3		A
V	Battery Short-Circuit Threshold	V <sub>BAT</sub> Rising	1.95	2.00	2.05	v
V <sub>SHORT</sub>	Hysteresis	V <sub>BAT</sub> Falling		100		
I <sub>SHORT</sub>	Short-Circuit Current	V <sub>BAT</sub> < V <sub>SHORT</sub>	20	30	40	mA
<b>т</b>	Thermal Shutdown Threshold <sup>(5)</sup>	TJ Rising		165		°C
T <sub>SHUTDWN</sub>	Hysteresis <sup>(5)</sup>	TJ Falling		10		
T <sub>CF</sub>	Thermal Regulation Threshold <sup>(5)</sup>	Charge Current Reduction Begins		120		°C
t <sub>INT</sub>	Detection Interval			2.1		S
t <sub>32SEC</sub>	32-Second Timer	32-Second Mode <sup>(6)</sup>	21.0		31.5	S
t <sub>15MIN</sub>	15-Minute Timer	15-Minute Mode	12.0	13.5	15.0	min

#### Notes:

3. Negative current is current flowing from the battery to the VIN pin (discharging the battery).

4. Q2 always turns on for 60 ns, then turns off if current is below I<sub>SYNC</sub>.

5. Guaranteed by design.

6. This tolerance applies to all timers on the IC, including soft-start and deglitching timers.

# I<sup>2</sup>C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
		Standard Mode			100	
£	SCL Clock Frequency	Fast Mode			400	
f <sub>SCL</sub>		High-Speed Mode, C <sub>B</sub> ≤ 100 pF			3400	kHz
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF			1700	
1	Bus-Free Time Between STOP	Standard Mode		4.7		
t <sub>BUF</sub>	and START Conditions	Fast Mode		1.3		μs
		Standard Mode		4		μs
t <sub>HD;STA</sub>	START or Repeated START Hold Time	Fast Mode		600		ns
		High-Speed Mode		160		ns
		Standard Mode		4.7		μs
		Fast Mode		1.3		μs
t <sub>LOW</sub>	SCL LOW Period	High-Speed Mode, C <sub>B</sub> ≤ 100 pF		160		ns
		High-Speed Mode, $C_B \le 400 \text{ pF}$		320		ns
		Standard Mode		4		μs
t <sub>HIGH</sub> SCL HIGH Period		Fast Mode		600		ns
	SCL HIGH Period	High-Speed Mode, $C_B \leq 100 \text{ pF}$		60		ns
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		120		ns
t <sub>SU:STA</sub> Repeated START Setup Time		Standard Mode		4.7		μs
	Fast Mode		600		ns	
·		High-Speed Mode		160		ns
		Standard Mode		250		
t <sub>su;dat</sub>	Data Setup Time	Fast Mode		100		ns
		High-Speed Mode		10		
		Standard Mode	0		3.45	μs
		Fast Mode	0		900	ns
t <sub>HD;DAT</sub>	Data Hold Time	High-Speed Mode, C <sub>B</sub> ≤ 100 pF	0		70	ns
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF	0		150	ns
		Standard Mode	20+0	.1C <sub>B</sub>	1000	
		Fast Mode	20+0	.1C <sub>B</sub>	300	
t <sub>RCL</sub>	SCL Rise Time	High-Speed Mode, $C_B \le 100 \text{ pF}$		10	80	ns
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		20	160	
		Standard Mode	20+0	.1C <sub>B</sub>	300	
		Fast Mode	20+0	.1C <sub>B</sub>	300	
t <sub>FCL</sub>	SCL Fall Time	High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	40	ns
		High-Speed Mode, $C_B \le 400 \text{ pF}$		20	80	
	SDA Bigg Time	Standard Mode	20+0	.1C <sub>B</sub>	1000	
t <sub>RDA</sub>	SDA Rise Time, Rise Time of SCL After a	Fast Mode	20+0	.1C <sub>B</sub>	300	
t <sub>RCL1</sub>	Repeated START Condition and	High-Speed Mode, $C_B \le 100 \text{ pF}$		10	80	ns
	After ACK Bit	High-Speed Mode, C <sub>B</sub> ≤ 400 pF		20	160	

Continued on the following page...

# I<sup>2</sup>C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
		Standard Mode	20+0.	1C <sub>B</sub>	300	
t <sub>FDA</sub>		Fast Mode	20+0.	1С <sub>в</sub>	300	
	SDA Fall Time	High-Speed Mode, C <sub>B</sub> ≤ 100 pF		10	80	ns
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		20	160	
	Stop Condition Setup Time	Standard Mode		4		μs
t <sub>su;sto</sub>		Fast Mode		600		ns
		High-Speed Mode		160		ns
C <sub>B</sub>	Capacitive Load for SDA and SCL				400	pF

# **Timing Diagrams**







10

# **Typical Characteristics**

Unless otherwise specified, circuit of Figure 1,  $V_{OREG}$  = 4.2 V,  $V_{IN}$  = 5.0 V, and  $T_A$ =25°C.





88

15



Figure 9. Charger Efficiency, I<sub>OCHARGE</sub>=1,550 mA





Figure 10. V<sub>IN</sub> Current in High-Impedance Mode, V<sub>BAT</sub>=3.6 V

Figure 11. Battery Current in High-Impedance Mode,  $V_{IN}$ =Open

# **Typical Characteristics**

Unless otherwise specified, circuit of Figure 1,  $V_{OREG}$  = 4.2 V,  $V_{IN}$  = 5.0 V, and  $T_A$ =25°C.



Charger / Adaptor, V<sub>BAT</sub>=3.4 V

Figure 15. Charger Startup with HZ\_MODE Bit Reset, I<sub>OCHARGE</sub>=950 mA, V<sub>OREG</sub>=4.2 V, V<sub>BAT</sub>=3.6 V

## **Typical Characteristics**

Unless otherwise specified, circuit of Figure 1,  $V_{OREG}$  = 4.2 V,  $V_{IN}$  = 5.0 V, and  $T_A$ =25°C.



Figure 16. No Battery at V<sub>IN</sub> Power-up



Figure 17. Non-Compliant Charger Rejection, VBAT=3.4 V



Figure 18. Battery Removal / Insertion During Charging, V<sub>BAT</sub>=3.9 V, I<sub>OCHARGE</sub>=950 mA, TE=0



Figure 19. Battery Removal / Insertion During Charging, V<sub>BAT</sub>=3.9 V, I<sub>OCHARGE</sub>=950 mA, TE=1

# **Circuit Description / Overview**

The FAN5421 is a highly integrated synchronous buck regulator for charging that can accommodate a wide range of input sources, including USB and current-limited "wall wart" power sources. The regulator employs synchronous rectification to maintain high efficiency over a wide range of battery voltages and charge states.

When charging batteries with a current-limited input source, the switching charger's high efficiency over a wide range of output voltages minimizes charging time.

The FAN5421 has two operating modes:

- 1. Charge Mode: Charges a single-cell Li-lon or Li-polymer battery.
- 2. High-Impedance Mode: The charging circuits are off in this mode. Current flow from VIN to the battery or from the battery to VIN is blocked in this mode. This mode consumes very little current from VIN or the battery.

#### **Charge Mode**

In Charge Mode, FAN5421 employs four regulation loops:

- 1. Charging Current: Limits the maximum charging current. This current is sensed using an external R<sub>SENSE</sub> resistor.
- Charge Voltage: The regulator is restricted from exceeding this voltage. As the internal battery voltage rises, the battery's internal impedance and R<sub>SENSE</sub> work in conjunction with the charge voltage regulation to decrease the amount of current flowing to the battery. Battery charging is completed when the voltage across R<sub>SENSE</sub> drops below the I<sub>TERM</sub> threshold.
- Temperature: If the IC's junction temperature reaches 120°C, charge current is continuously reduced until the IC's temperature stabilizes at 120°C.
- 4. VIN: This loop limits the amount of drop on VIN to a programmable voltage ( $V_{SP}$ ) to accommodate "special chargers" that limit current to a lower current than might be available from a "normal" wall charger.

#### **Battery Charging Curve**

If the battery voltage is below V<sub>SHORT</sub>, a linear current source "pre-charges" the battery until V<sub>BAT</sub> reaches V<sub>SHORT</sub>. The PWM charging circuit is then started and the battery is charged with a constant current if sufficient input power is available. Current slew rate is limited to prevent overshoot.

The FAN5421 is designed to work with a current-limited input source at VIN. During the current regulation phase of charging, the input power source may limit the amount of current available to charge the battery and power the system. The effect of input current limit on  $I_{CHARGE}$  can be seen in Figure 21.



#### Figure 20. Charge Curve When Source Current Does Not Limit I<sub>CHARGE</sub>



# Figure 21. Charge Curve When Input Source Limits I<sub>CHARGE</sub>

Assuming  $V_{OREG}$  is programmed to the cell's fully charged "float" voltage, the current that the battery accepts with the PWM regulator limiting its output (sensed at VBAT) to  $V_{OREG}$  declines and the charger enters voltage regulation phase of charging. When the current declines to the programmed  $I_{TERM}$  value, the charge cycle is complete. Charge current termination can be disabled by resetting the TE bit (REG1[3]).

The charger output or "float" voltage can be programmed by the OREG bits from 3.5 V to 4.44 V in 20 mV increments, as shown in Table 3.

# Table 3. OREG Bits ( <code>OREG[7:2]</code> ) vs. Charger $V_{\text{OUT}}$ (V\_{<code>OREG</code>) Float Voltage

(VOREG) Hour Vorage						
Decimal	Hex	$\mathbf{V}_{OREG}$		Decimal	Hex	$\mathbf{V}_{OREG}$
0	00	3.50		32	20	4.14
1	01	3.52		33	21	4.16
2	02	3.54		34	22	4.18
3	03	3.56		35	23	4.20
4	04	3.58		36	24	4.22
5	05	3.60		37	25	4.24
6	06	3.62		38	26	4.26
7	07	3.64		39	27	4.28
8	08	3.66		40	28	4.30
9	09	3.68		41	29	4.32
10	0A	3.70		42	2A	4.34
11	0B	3.72		43	2B	4.36
12	0C	3.74		44	2C	4.38
13	0D	3.76		45	2D	4.40
14	0E	3.78		46	2E	4.42
15	0F	3.80		47	2F	4.44
16	10	3.82		48	30	4.44
17	11	3.84		49	31	4.44
18	12	3.86		50	32	4.44
19	13	3.88		51	33	4.44
20	14	3.90		52	34	4.44
21	15	3.92		53	35	4.44
22	16	3.94		54	36	4.44
23	17	3.96		55	37	4.44
24	18	3.98		56	38	4.44
25	19	4.00		57	39	4.44
26	1A	4.02		58	3A	4.44
27	1B	4.04		59	3B	4.44
28	1C	4.06		60	3C	4.44
29	1D	4.08		61	3D	4.44
30	1E	4.10		62	3E	4.44
Note:			•	-		

#### Note:

7. Default register settings are denoted by **bold typeface**.

The charging parameters in Table 4 can be programmed by the host through the  $l^2C$  interface.

## Table 4. Programmable Charging Parameters

Parameter	Name	Register
Output Voltage Regulation	V <sub>OREG</sub>	REG2[7:2]
Battery Charging Current Limit	I <sub>OCHRG</sub>	REG4[6:4]
Charge Termination Limit	I <sub>TERM</sub>	REG4[2:0]
Weak Battery Voltage	V <sub>LOWV</sub>	REG1[5:4]

A new charge cycle begins when one of the following occurs:

- 1. The battery voltage falls below  $V_{\text{OREG}}$   $V_{\text{RCH}}$
- 2.  $V_{IN}$  Power-On-Reset (POR) clears and the battery voltage is below the weak battery threshold ( $V_{LOWV}$ ).
- 3. The  $\overline{CE}$  or RESET bit is set.

## **Charge Current Limit**

# Table 5. $I_{\text{OCHARGE}}$ Current as a Function of the IOCHARGE Bits and $R_{\text{SENSE}}$ Resistor Value

DEC	BIN	HEX	V <sub>RSENSE</sub>	I <sub>OCHAR</sub>	<sub>GE</sub> (mA)
DEC	DIN		(mV)	68 mΩ	100 mΩ
0	0000	00	37.4	550	374
1	0001	01	44.2	650	442
2	0010	02	51.0	750	510
3	0011	03	57.8	850	578
4	0100	04	64.6	950	646
5	0101	05	71.4	1,050	714
6	0110	06	78.2	1,150	782
7	0111	07	85.0	1,250	850
8	1000	08	91.8	1,350	918
9	1001	09	98.6	1,450	986
10	1010	0A	105.4	1,550	1,054
11	1011	0B	105.4	1,550	1,054
12	1100	0C	105.4	1,550	1,054
13	1101	0D	105.4	1,550	1,054
14	1110	0E	105.4	1,550	1,054
15	1111	0F	105.4	1,550	1,054

## **Termination Current Limit**

Current charge termination is enabled when TE ( REG1[3] ) = 1. Typical termination current values are given in Table 6.

ITERM		BIN	HEX		V <sub>RSENSE</sub>		ı (mA)
	DIN	пех		(mV)	68 mΩ	100 mΩ	
0	000	00	3.3	49	33		
1	001	01	6.6	97	66		
2	010	02	9.9	146	99		
3	011	03	13.2	194	132		
4	100	04	16.5	243	165		
5	101	05	19.8	291	198		
6	110	06	23.1	340	231		
7	111	07	26.4	388	264		

# Table 6. $I_{\text{TERM}}$ Current as a Function of the ITERM Bits ( REG4[2:0] ) and $R_{\text{SENSE}}$ Resistor Value

When the charge current falls below  $I_{TERM}$ , PWM charging stops and the STAT bits change to READY (00) for about 500ms while the IC determines whether the battery and charging source are still connected. If they are, STAT then changes to CHARGE DONE (10).

#### **PWM Controller in Charge Mode**

The IC uses a current-mode PWM controller to regulate the output voltage and battery charge currents. A cycle-by-cycle current limit of nominally 2.3 A, sensed through Q1, is used to terminate  $t_{ON}$ . The synchronous rectifier (Q2) also has a current limit that turns off Q2 at 100 mA to prevent current flow from the battery.

#### Safety Timer see Figure 26

At the beginning of charging process, the IC starts a 15minute timer ( $t_{15MIN}$ ). When this timer expires, charging is terminated. Writing to any register through I<sup>2</sup>C stops the  $t_{15MIN}$  timer, which then starts a 32-second timer ( $t_{32SEC}$ ). Setting the TMR\_RST bit ( REG0[7] ) resets the  $t_{32SEC}$  timer. If the  $t_{32SEC}$  timer expires; charging is terminated, the registers are set to default values, and charging resumes using the default values with the  $t_{15MIN}$  timer running.

Normal charging is controlled by the host with the  $t_{\rm 32SEC}$  timer running to ensure that the host is alive. Charging with the  $t_{\rm 15MIN}$  timer running is used for charging that is unattended by the host. If the 15-minute timer expires; the IC turns off the charger, sets the  $\overline{CE}$  bit, and indicates a timer fault (110) on the FAULT bits ( REG0[2:0] ). This sequence prevents overcharge if the host fails to reset the  $t_{\rm 32MIN}$  timer.

## V<sub>IN</sub> POR / Non-Compliant Charger Rejection

When the IC detects that V<sub>IN</sub> has risen above V<sub>IN(MIN)1</sub> (4.4 V), the IC applies a 110  $\Omega$  load from VIN to GND. To clear the V<sub>IN</sub> Power-On-Reset (POR) and begin charging, V<sub>IN</sub> must remain above V<sub>IN(MIN)2</sub> (4.1 V) and below VIN<sub>OVP</sub> for t V<sub>IN\_VALID</sub> (30 ms). The V<sub>IN</sub> validation sequence always occurs before charging is initiated or re-initiated (for example, after a V<sub>IN</sub> OVP fault or a V<sub>RCH</sub> recharge initiation).

 $t_{\text{VIN\_VALID}}$  ensures that unfiltered 50 / 60 Hz chargers and other non-compliant chargers are rejected.

#### **Boot Sequence**

At VIN POR, when the battery voltage is above the weak battery threshold (VLOWV), the IC operates in accordance with its I<sup>2</sup>C register settings. If V<sub>BAT</sub> < V<sub>LOWV</sub>, the IC sets all registers to their default values and enables the charger. This feature can revive a cell whose voltage is too low to ensure reliable host operation. Charging continues in the absence of host communication even after the battery has reached V<sub>OREG</sub>, whose default value is 3.54 V, and the charger remains active until t<sub>15MIN</sub> expires. Once the host processor begins writing to the IC, charging parameters are set by the host, which must continually reset the t<sub>32SEC</sub> timer by writing to the TMR RST bit to continue charging using the programmed charging parameters. If t<sub>32SEC</sub> expires, the register defaults are loaded, the FAULT bits are set to 110, STAT is pulsed HIGH, and charging continues with default charging parameters.





Figure 23. Charge Configuration State

Figure 24. HZ State





#### Current Limited Charger: V<sub>SP</sub> Loop

The FAN5421 can accommodate current-limited input supplies by reducing the charging current to prevent  $V_{\text{BUS}}$  from falling below a specified limit. When a current-limited charger is supplying  $V_{\text{IN}}$ , the IC slowly increases the charging current until either:

- I<sub>OCHARGE</sub> is reached, or
- V<sub>IN</sub> = V<sub>SP</sub>.

If  $V_{\rm IN}$  collapses to  $V_{\rm SP}$  when current is ramping up, the IC charges with an input current that keeps  $V_{\rm IN} = V_{\rm SP}$ . When the  $V_{\rm SP}$  control loop is limiting the charge current, the SP bit (REG5[4]) is set.

Table 7. V<sub>SP</sub> as a Function of SP Bits (REG5[2:0])

BIN 000 001	HEX 00 01	V <sub>SP</sub> 4.20 4.28
001		-
	01	4.28
010	02	4.36
011	03	4.44
100	04	4.52
101	05	4.60
110	06	4.68
111	07	4.76
	<b>100</b> 101 110	100         04           101         05           110         06

#### **Safety Settings**

The IC contains a SAFETY register ( REG6 ) that prevents the values in OREG (  $\mathsf{REG2}[7:2]$  ) and IOCHARGE (  $\mathsf{REG4}[7:4]$  ) from exceeding the VSAFE and ISAFE values.

After  $V_{BAT}$  rises above  $V_{SHORT}$ , the SAFETY register is loaded with its default value and may be written only before another register is written. After writing to any other register, the SAFETY register is locked until  $V_{BAT}$  falls below  $V_{SHORT}$ .

The ISAFE (REG6[6:4]) and VSAFE (REG6[3:0]) establish values that limit the maximum values of  $I_{OCHARGE}$  and  $V_{OREG}$  used by the control logic. If the host attempts to write a value higher than VSAFE or ISAFE to OREG or IOCHARGE, respectively, the VSAFE or ISAFE value appears as the OREG and IOCHARGE register value, respectively.

Table 8. I <sub>SAFE</sub> (I <sub>OCHARGE</sub> )	Limit) as	a Function	of ISAFE
Bits ( REG6[7:4] )			

ISAFE ( REG6[7:4] )					
DEC	BIN	HEX	V <sub>RSENSE</sub>	I <sub>SAFE</sub>	(mA)
DEC	DIN		(mV)	68 mΩ	100 mΩ
0	0000	00	37.4	550	374
1	0001	01	44.2	650	442
2	0010	02	51.0	750	510
3	0011	03	57.8	850	578
4	0100	04	64.6	950	646
5	0101	05	71.4	1,050	714
6	0110	06	78.2	1,150	782
7	0111	07	85.0	1,250	850

 Table 8. I<sub>SAFE</sub> (I<sub>OCHARGE</sub> Limit) as a Function of ISAFE
 Bits ( REG6[7:4] )

ISAFE (REG0[7:4])					
DEC		HEX	V <sub>RSENSE</sub>	I <sub>SAFE</sub>	(mA)
DEC	BIN		(mV)	68 mΩ	100 mΩ
8	1000	17	91.8	1,350	918
9	1001	18	98.6	1,450	986
10	1010	19	105.4	1,550	1,054
11	1011	1A	112.2	1,650	1,122
12	1100	1B	119.0	1,750	1,190
13	1101	1C	125.8	1,850	1,258
14	1110	1D	132.6	1,950	1,326
15	1111	1E	139.4	2,050	1,394

# Table 9. $V_{SAFE}$ ( $V_{OREG}$ Limit) as a Function of VSAFE Bits ( REG6[3:0] )

VSAFE (REG6[3:0])

ISAEE ( DEC6[7:41)

		/		
DEC	BIN	HEX	Max. OREG ( REG2[7:2] )	V <sub>oreg</sub> Max.
0	0000	00	100011	4.20
1	0001	01	100100	4.22
2	0010	02	100101	4.24
3	0011	03	100110	4.26
4	0100	04	100111	4.28
5	0101	05	101000	4.30
6	0110	06	101001	4.32
7	0111	07	101010	4.34
8	1000	08	101011	4.36
9	1001	09	101100	4.38
10	1010	0A	101101	4.40
11	1011	0B	101110	4.42
12	1100	0C	101111	4.44
13	1101	0D	110000	4.44
14	1110	0E	110001	4.44
15	1111	0F	110010	4.44

### **Thermal Regulation and Protection**

When the IC's junction temperature reaches  $T_{CF}$  (about 120°C), the charger reduces its output current to prevent overheating. If the temperature continues to increase, the current is reduced to 0 when the junction is 10°C above  $T_{CF}$ . If the temperature increases beyond  $T_{SHUTDOWN}$ ; charging is suspended, the FAULT bits are set to 101, and STAT is pulsed HIGH. In Suspend Mode, all timers stop and the state of the IC's logic is preserved. Charging resumes after the die cools to about 10°C below  $T_{SHUTDOWN}$ .

#### **Charge Mode Input Supply Protection**

#### Sleep Mode

When V<sub>IN</sub> falls below V<sub>BAT</sub> + V<sub>SLP</sub> and V<sub>IN</sub> is above V<sub>IN(MIN)</sub>, the IC enters Sleep Mode to prevent the battery from draining into VIN. During Sleep Mode, reverse current is disabled by turning off Q3.

#### Input Supply Low-Voltage Detection

The IC continuously monitors  $V_{\text{IN}}$  during charging. If  $V_{\text{IN}}$  falls below  $V_{\text{IN}(\text{MIN})}$ ; the IC terminates charging and pulses the STAT pin HIGH, sets STAT bits to 11, and sets the FAULT bits to 011.

If  $V_{\text{IN}}$  recovers above the  $V_{\text{IN}(\text{MIN})}$  rising threshold after timer  $t_{\text{INT}}$  (about two seconds), the charging process is repeated. This function prevents the input power bus from collapsing or oscillating when the IC is connected to a suspended USB port or a low-current-capable OTG device.

#### Input Over-Voltage Detection

When  $V_{IN}$  exceeds  $VIN_{OVP}$ , the IC:

- 1. Turns off Q3,
- 2. Suspends charging, and
- 3. Sets the FAULT bits to 001, STAT bits to 11, and pulses the STAT pin.

When  $V_{IN}$  falls about 130mV below VIN<sub>OVP</sub>, the fault is cleared and charging resumes after VIN is revalidated (seeVIN POR / Non-Compliant Charger Rejection above).

# Charge Mode Battery Detection and Protection

#### **V**<sub>BAT</sub> Over-Voltage Protection (OVP)

The OREG voltage regulation loop prevents  $V_{BAT}$  from overshooting the OREG voltage by more than 50 mV when the battery is removed. When the PWM charger is running with no battery, the TE bit is not set, and a battery is inserted that's charged to a voltage higher than  $V_{OREG}$ ; PWM pulses stop. If no further pulses occur for 30ms, the IC sets the FAULT bits to 100, STAT bits to 11, and pulses the STAT pin.

#### **Battery Detection During Charging**

The IC can detect presence, absence, or removal of a battery if the termination bit is set (TE=1). During normal charging; once V<sub>BAT</sub> is close to V<sub>OREG</sub> and the termination charge current is detected, the IC terminates charging and sets the STAT bits to 10. It then turns on a discharge current, I<sub>DETECT</sub>, for t<sub>DETECT</sub>. If V<sub>BAT</sub> is still above V<sub>OREG</sub> – V<sub>RCH</sub>, the battery is present and the IC sets the FAULT bits to 000. If V<sub>BAT</sub> is below V<sub>OREG</sub> – V<sub>RCH</sub>, the battery is absent and the IC:

- 1. Sets the registers to their default values,
- 2. Sets the FAULT bits to 111, and
- 3. Resumes charging with default values after delay  $t_{\text{INT}}$ .

If the battery is removed while charging with TE = 0, charging continues and  $V_{\text{BAT}}$  is regulated to  $V_{\text{OREG}}.$ 

#### System Operation with No Battery

The IC continues charging after VIN POR with the default parameters, regulating the  $V_{BAT}$  line to 3.54 V until the host processor issues commands or the 15-minute timer expires. In this way, the IC can start the system without a battery.

By default, the system current is limited to 325 mA. To increase the current limit, use the following sequence.

- 1. Program the Safety Register.
- 2. Set OREG to the desired value (typically 4.18).
- 3. Set IOCHARGE, then reset the IOLEVEL bit.

#### **Battery Short-Circuit Protection**

If the battery voltage is below the short-circuit threshold (V<sub>SHORT</sub>); a linear current source, I<sub>SHORT</sub>, supplies V<sub>BAT</sub> until V<sub>BAT</sub> > V<sub>SHORT</sub>.

#### **Charger Status / Fault Status**

The STAT pin indicates the operating condition of the IC and provides a fault indicator for interrupt driven systems.

#### **Table 10. STAT Pin Function**

EN_STAT	Charge State	STAT Pin
0	Х	OPEN
Х	Normal Conditions	OPEN
1	Charging	LOW
Х	Fault	128 $\mu s$ Pulse, then OPEN

The FAULT bits (  ${\sf R0}[2:0]$  ) indicate the type of fault in Charge Mode, as shown in Table 11.

#### Table 11. Fault Status Bits

I	Fault Bit		Fault Description
B2	B1	B0	Fault Description
0	0	0	Normal (No Fault)
0	0	1	V <sub>BUS</sub> OVP
0	1	0	Sleep Mode
0	1	1	Poor Input Source
1	0	0	Battery OVP
1	0	1	Thermal Shutdown
1	1	0	Timer Fault
1	1	1	No Battery

#### **Charge Control Bits**

The following table defines the CE and RESET bit functions.

#### Table 12. Charge Control Bits

Bit	Reg	State	Function
CE	REG0[2]	0	Charging Enabled
CE		CE REGU[2]	1
RESET	REG4[7]	1	Writing 1 resets all registers to their default values

CE is set by the FAN5421 when  $t_{15MIN}$  timer overflows.

#### Table 13. DISABLE Pin and $\overline{CE}$ Bit Functionality

Charging	DISABLE PIN	CE BIT: REG 01[2]
ENABLE	0	0
DISABLE	Х	1
DISABLE	1	Х

#### **VREF PIN**

The VREF pin is powered from PMID and is on only when PMID > V<sub>BAT</sub> and does not drain current from the battery. The IC uses this pin for its bias supply. Its output is about 350 mV below PMID as long as PMID < 5.6 V. If V<sub>BUS</sub> / PMID rise above 5.6 V, the VREF pin remains below 5.35 V.

## I<sup>2</sup>C Interface

The FAN5421 serial interface is compatible with Standard, Fast, Fast-Plus, and High-Speed (HS) Mode I<sup>2</sup>C-Bus<sup>®</sup> specifications. The SCL line is an input. The SDA line is a bidirectional open-drain output; it can only pull down the bus when active. The SDA line only pulls LOW during data reads and when signaling ACK. All data is shifted in MSB (bit 7) first.

#### Table 14, I<sup>2</sup>C Slave Address

7	6	5	4	3	2	1	0
1	1	0	1	0	1	0	R/W

In Hex notation, the slave address assumes a 0 LSB. The hex slave address is D4H.

#### **Bus Timing**

As shown in Figure 27, data is normally transferred when SCL is LOW. Data is clocked in on the rising edge of SCL. Typically, data transitions shortly at or after the falling edge of SCL to allow ample time for the data to set up before the next SCL rising edge.



Figure 27. Data Transfer Timing

Each bus transaction begins and ends with SDA and SCL HIGH. A transaction begins with a "START" condition, which is defined as SDA transitioning from 1 to 0 with SCL HIGH, as shown in Figure 28.





A transaction ends with a "STOP" condition, which is defined as SDA transitioning from 0 to 1 with SCL HIGH, as shown in Figure 29.



During a read from the FAN5421 (Figure 32), the master issues a "REPEATED START" after sending the register address and before resending the slave address. The "REPEATED START" is a 1-to-0 transition on SDA while SCL is HIGH, as shown in Figure 30.

#### High-Speed (HS) Mode

The protocols for High-Speed (HS), Low-Speed (LS), and Fast-Speed (FS) Modes are identical; except the bus speed for HS mode is 3.4 MHz. HS Mode is entered when the bus master sends the HS master code 00001XXX after a START condition. The master code is sent in Fast or Fast-Plus Mode (less than 1 MHz clock) and slaves do not ACK this transmission.

The master then generates a REPEATED START condition (Figure 30) that causes all slaves on the bus to switch to HS Mode. The master then sends I<sup>2</sup>C packets, as described above, using the HS Mode clock rate and timing.

The bus remains in HS Mode until a stop bit (Figure 29) is sent by the master. While in HS Mode, packets are separated by REPEATED START conditions (Figure 30).



Figure 30. REPEATED START Timing

#### Read and Write Transactions

The following figures outline the sequences for data read and write. Bus control is signified by the shading of the packet,

defined as	Master Drives Bus	and	Slave Drives Bus					
uchinea as		ana						
All addresses and data are MSB first								

#### Table 15. Bit Definitions for Figure 31, Figure 32

Symbol	Definition
S	START, see Figure 28
А	ACK. The slave drives SDA to 0 to acknowledge the preceding packet.
Ā	NACK. The slave sends a 1 to NACK the preceding packet.
R	REPEATED START, see Figure 30
Р	STOP, see Figure 29

# **Register Descriptions**

FAN5421 has seven user-accessible registers, described in Table 16.

# Table 16. I<sup>2</sup>C Register Address

R	Address Bits								
Name	REG#	7	6	5	4	3	2	1	0
CONTROL0	0	0	0	0	0	0	0	0	0
CONTROL1	1	0	0	0	0	0	0	0	1
OREG	2	0	0	0	0	0	0	1	0
IC_INFO	3	0	0	0	0	0	0	1	1
IBAT	4	0	0	0	0	0	1	0	0
SP_CHARGER	5	0	0	0	0	0	1	0	1
SAFETY	6	0	0	0	0	0	1	1	0

#### **Register Bit Definitions**

The following table defines the operation of each register bit for all IC versions. Default values are in **bold** text.

Bit	Name	Value	Туре	Description					
CON	ITROL0			Register Add	ress: 00 Default Value =X1XX 0XXX				
7	TMR_RST	1	W	Writing a 1 re	esets the t <sub>32SEC</sub> timer. Writing a 0 has no effect.				
'	SRST	R		Returns the S	SRST pin level (1 = HIGH).				
6	EN_STAT	0	R/W		T pin function. STAT = OPEN				
0		1		Enables ST	AT pin function				
		00	R	Ready					
E . A	STAT	01		Charge in pro	ge in progress				
5.4	SIAI	10		Charge done					
		11		Fault					
3	Reserved	0	R	This bit is dis	abled and always returns 0 when read back.				
2:0	FAULT		R	Fault status b	bits: see Table 11				
CON	ITROL1			Register Add	ress: 01 Default Value = 0011 0000 (30H)				
7:6	Reserved	00	R/W	These bits ha	hese bits have no effect on the IC operation.				
	V <sub>LOWV</sub>	00	R/W	3.4 V					
5.1		01		3.5 V	Weak battery voltage threshold				
J. <del>4</del>		10		3.6 V					
		11		3.7 V					
3	TE	0	R/W	Disable cha	rge current termination				
5		1		Enable charg	e current termination				
2		0	R/W	Charger ena	bled				
2	CE	1		Charger disa	bled				
1	HZ_MODE	0	R/W	Not High-Im	pedance Mode				
I		1		High-Impeda	nce Mode				
0	Reserved	0	R	This bit is disabled and always returns 0 when read back.					
ORE	G			Register Add	ress: 02 Default Value = 0000 1010 (0AH)				
7:2	OREG		R/W		Charger output "float" voltage. Programmable from 3.5 to 4.44 V in 20 mV increments. Defaults to 000010 (3.54 V): see Table 3.				
	Reserved	10	R	These bits are disabled and always returns 10 when read back.					

Continued on the following page...

# Register Bit Definitions (Continued)

The following table defines the operation of each register bit for all IC versions. Default values are in **bold** text.

Bit	Name	Value	Туре	Description				
IC_II	NFO	1		Register Address: 03 Default Value = 1001 0XXX				
7:5	Vendor Code	100	R	Identifies Fairchild Semiconductor as the IC supplier.				
4:3	PN	00	R	art number bits				
2:0	REV		R	IC Revision. Revision is 1.X, where X is the decimal of these 3 bits.				
<b>IBA</b>	<b>F</b>			Register Address: 04 Default Value = 1000 0001 (81H)				
7	RESET	1	W	Writing a 1 resets all registers parameters, except the Safety register (Reg6), to their defaults. Writing a 0 has no effect. Read returns 1.				
6:3	IOCHARGE	Table 5	R/W	Programs the maximum charge current, see Table 5.				
2:0	ITERM	Table 6	R/W	Sets the current used for charging termination, see Table 6.				
SP_	CHARGER			Register Address: 05 Default Value = 0010 XX00				
7:6	Reserved	0	R	This bit is disabled and always returns 0 when read back.				
		0		Output current is controlled by IOCHARGE bits.				
5	5 IO_LEVEL 1 R/W		R/W	Voltage across $R_{SENSE}$ for output current control is set to 22.1 mV (325 mA for $R_{SENSE}$ =68 m $\Omega$ , 221 mA for 100 m $\Omega$ ).				
4	0	R	Special charger is not active ( $V_{BUS}$ is able to stay above $V_{SP}$ ).					
4	SP	1	ĸ	Special charger has been detected and $V_{BUS}$ is being regulated to $V_{SP}$ .				
		0	Б	DISABLE pin is LOW.				
3	3 EN_LEVEL		R	DISABLE pin is HIGH.				
2:0	VSP	Table 7	R/W	Special charger input regulation voltage, see Table 7.				
SAF	ETY			Register Address: 06 Default Value = 0100 0000 (40H)				
7:4	ISAFE	Table 8	R/W	Sets the maximum I <sub>OCHARGE</sub> value used by the control circuit, see Table 8.				
3:0	VSAFE	Table 9	R/W	Sets the maximum V <sub>OREG</sub> used by the control circuit, see Table 9.				

# **PCB Layout Recommendations**

Bypass capacitors should be placed as close to the IC as possible.

In particular, the total loop length for CMID should be minimized to reduce overshoot and ringing on the SW, PMID, and VBUS pins.

All power and ground pins must be routed to their bypass capacitors using top copper if possible. Copper area connecting to the IC should be maximized to improve thermal performance.



Figure 33. PCB Layout Recommendations



Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings: <u>http://www.fairchildsemi.com/packaging/.</u>

#### 

U

FAN5421

L

Single-Cell Li-Ion Switching Charger

#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool AccuPower<sup>™</sup> AX-CAP®\* BitSiC™ Build it Now CorePLUS<sup>TI</sup> **CorePOWER™** CROSSVOLT CTL™ Current Transfer Logic™ DEUXPEED® Dual Cool™ **EcoSPARK<sup>®</sup>** EfficientMax™ ESBC R Fairchild® Fairchild Semiconductor® FACT Quiet Series™ FACT<sup>®</sup> FAST<sup>®</sup> FastvCore™ FETBench™

**FPS**<sup>TM</sup> F-PFS FRFET® Global Power Resource GreenBridge Green FPST Green FPS™ e-Series™ Gmax GTO™ IntelliMAX<sup>™</sup> **ISOPLANAR**<sup>TM</sup> Making Small Speakers Sound Louder and Better<sup>T</sup> MegaBuck<sup>™</sup> MICROCOUPLER MicroFET MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver™ OptoHiT™ OPTOLOGIC<sup>®</sup> **OPTOPLANAR**<sup>®</sup>

PowerTrench<sup>®</sup> PowerXS™ Programmable Active Droop™ QFET QST Quiet Series™ RapidConfigure™ Saving our world, 1mW/W/kW at a time™ SignalWise SmartMax™ SMART START Solutions for Your Success™ SPM® STEALTH SuperFET SuperSOT™-3 SuperSOT™-6 SuperSOT<sup>™</sup>-8 SupreMOS® SyncFET™



TinyCalc<sup>TM</sup> TinyLogic<sup>®</sup> TINYOPTO<sup>TM</sup> TinyPower<sup>TM</sup> TinyPWM<sup>TM</sup> TinyWire<sup>TM</sup> TranSiC<sup>TM</sup> TriFault Detect<sup>TM</sup> TRUECURRENT<sup>®</sup>\*  $\mu$ SerDes<sup>TM</sup>

UHC<sup>®</sup> Ultra FRFET™ UniFET™ VCX™ VisualMax™ VoltagePlus™ XS™

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

#### As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers by either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty overage or other assistance for parts bought from Unauthorized Sources. Fairchild to combat this global problem and encourage our customers to ot being this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS

Definition	on of	Terms	

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 164

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC